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***DISCRETE POWER DIODES and THYRISTORS***  
***DATA BOOK***

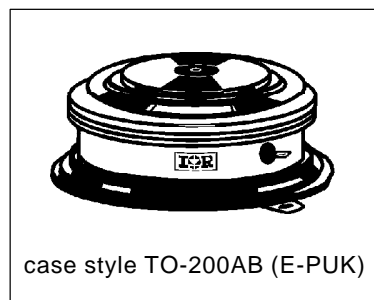
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**PHASE CONTROL THYRISTORS**
**Hockey Puk Version**
**Features**

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AB (E-PUK)

**650A**
**Typical Applications**

- DC motor controls
- Controlled DC power supplies
- AC controllers


**Major Ratings and Characteristics**

Parameters	ST300C..C	Units	
$I_{T(AV)}$	650	A	
@ $T_{hs}$	55	°C	
$I_{T(RMS)}$	1290	A	
@ $T_{hs}$	25	°C	
$I_{TSM}$	@ 50Hz	8000	A
	@ 60Hz	8380	A
$I^2t$	@ 50Hz	320	KA <sup>2</sup> s
	@ 60Hz	292	KA <sup>2</sup> s
$V_{DRM}/V_{RRM}$	400 to 2000	V	
$t_q$	typical	100	μs
$T_J$	- 40 to 125	°C	

## ST300C..C Series

### ELECTRICAL SPECIFICATIONS

#### Voltage Ratings

Type number	Voltage Code	$V_{DRM}/V_{RRM}$ , max. repetitive peak and off-state voltage V	$V_{RSM}$ , maximum non-repetitive peak voltage V	$I_{DRM}/I_{RRM}$ max. @ $T_J = T_J$ max mA
ST300C..C	04	400	500	50
	08	800	900	
	12	1200	1300	
	16	1600	1700	
	18	1800	1900	
	20	2000	2100	

#### On-state Conduction

Parameter	ST300C..C	Units	Conditions		
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	650 (320)	A	180° conduction, half sine wave double side (single side) cooled		
	55 (75)	°C			
$I_{T(RMS)}$ Max. RMS on-state current	1290	A	DC @ 25°C heatsink temperature double side cooled		
$I_{TSM}$ Max. peak, one-cycle non-repetitive surge current	8000		t = 10ms	No voltage	
	8380		t = 8.3ms	reapplied	
	6730		t = 10ms	100% $V_{RRM}$	
	7040		t = 8.3ms	reapplied	
$I^2t$ Maximum $I^2t$ for fusing	320		KA <sup>2</sup> s	t = 10ms	No voltage
	292			t = 8.3ms	reapplied
	226			t = 10ms	100% $V_{RRM}$
	207	t = 8.3ms		reapplied	
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	3200	KA <sup>2</sup> /s	t = 0.1 to 10ms, no voltage reapplied		
$V_{T(TO)1}$ Low level value of threshold voltage	0.97	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ max.		
$V_{T(TO)2}$ High level value of threshold voltage	0.98		$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ max.		
$r_{\theta 1}$ Low level value of on-state slope resistance	0.74	mΩ	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ max.		
$r_{\theta 2}$ High level value of on-state slope resistance	0.73		$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ max.		
$V_{TM}$ Max. on-state voltage	2.18	V	$I_{pk} = 1635A$ , $T_J = T_J$ max, $t_p = 10ms$ sine pulse		
$I_H$ Maximum holding current	600	mA	$T_J = 25^\circ C$ , anode supply 12V resistive load		
$I_L$ Typical latching current	1000				

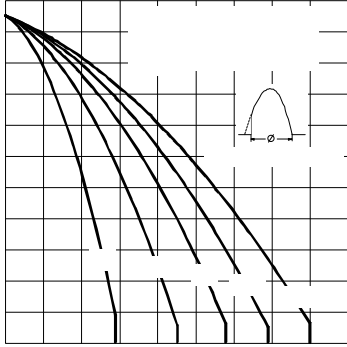


Fig. 3 - Current Ratings Characteristics

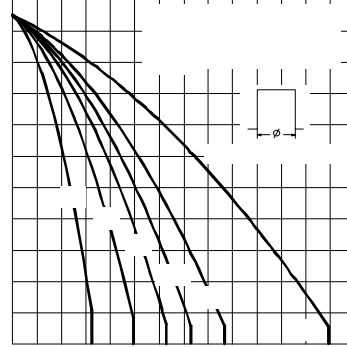


Fig. 4 - Current Ratings Characteristics

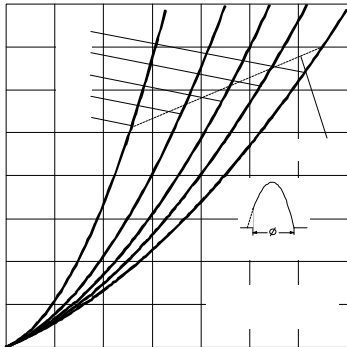


Fig. 5 - On-state Power Loss Characteristics

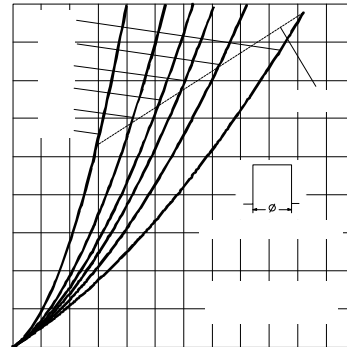


Fig. 6 - On-state Power Loss Characteristics

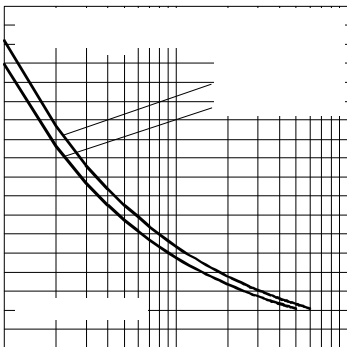


Fig. 7 - Maximum Non-Repetitive Surge Current  
Single and Double Side Cooled

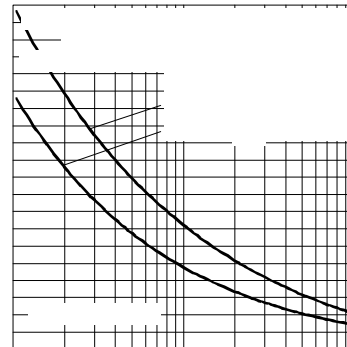


Fig. 8 - Maximum Non-Repetitive Surge Current  
Single and Double Side Cooled

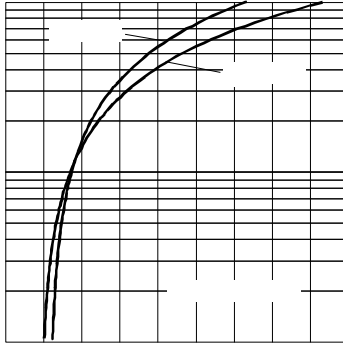


Fig. 9 - On-state Voltage Drop Characteristics

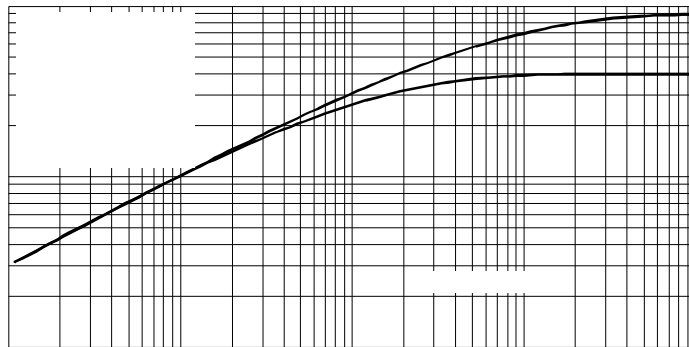


Fig. 10 - Thermal Impedance  $Z_{thJ-hs}$  Characteristics

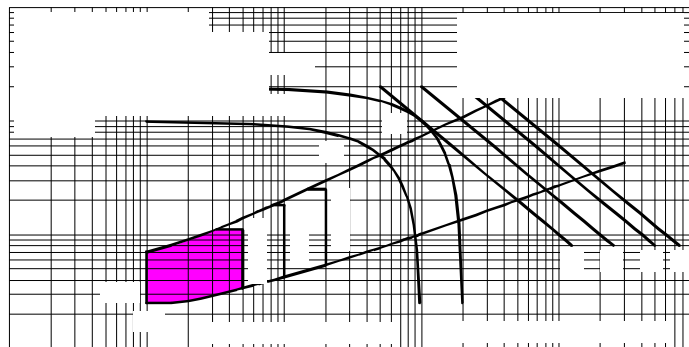


Fig. 11 - Gate Characteristics

## ST300C..C Series

### Switching

Parameter	ST300C..C	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$ $T_J = T_J \text{ max}$ , anode voltage $\leq 80\% V_{DRM}$
$t_d$ Typical delay time	1.0	μs	Gate current 1A, $di_g/dt = 1A/\mu s$ $V_d = 0.67\% V_{DRM}$ , $T_J = 25^\circ C$
$t_q$ Typical turn-off time	100		$I_{TM} = 300A$ , $T_J = T_J \text{ max}$ , $di/dt = 40A/\mu s$ , $V_R = 50V$ $dv/dt = 20V/\mu s$ , Gate 0V 100Ω, $t_p = 500\mu s$

### Blocking

Parameter	ST300C..C	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/μs	$T_J = T_J \text{ max}$ , linear to 80% rated $V_{DRM}$
$I_{RRM}$ $I_{DRM}$ Max. peak reverse and off-state leakage current	50	mA	$T_J = T_J \text{ max}$ , rated $V_{DRM}/V_{RRM}$ applied

### Triggering

Parameter	ST300C..C	Units	Conditions
$P_{GM}$ Maximum peak gate power	10.0	W	$T_J = T_J \text{ max}$ , $t_p \leq 5ms$
$P_{G(AV)}$ Maximum average gate power	2.0		$T_J = T_J \text{ max}$ , $f = 50Hz$ , $d\% = 50$
$I_{GM}$ Max. peak positive gate current	3.0	A	$T_J = T_J \text{ max}$ , $t_p \leq 5ms$
$+V_{GM}$ Maximum peak positive gate voltage	20	V	$T_J = T_J \text{ max}$ , $t_p \leq 5ms$
$-V_{GM}$ Maximum peak negative gate voltage	5.0		
$I_{GT}$ DC gate current required to trigger	TYP.	MAX.	$T_J = -40^\circ C$ $T_J = 25^\circ C$ $T_J = 125^\circ C$ Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
	200	-	
	100	200	
$V_{GT}$ DC gate voltage required to trigger	2.5	-	$T_J = -40^\circ C$ $T_J = 25^\circ C$ $T_J = 125^\circ C$
	1.8	3.0	
	1.1	-	
$I_{GD}$ DC gate current not to trigger	10.0	mA	$T_J = T_J \text{ max}$ Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated $V_{DRM}$ anode-to-cathode applied
$V_{GD}$ DC gate voltage not to trigger	0.25	V	

## ST300C..C Series

### Thermal and Mechanical Specification

Parameter	ST300C..C	Units	Conditions
T <sub>J</sub> Max. operating temperature range	-40 to 125	°C	
T <sub>stg</sub> Max. storage temperature range	-40 to 150		
R <sub>thJ-hs</sub> Max. thermal resistance, junction to heatsink	0.09 0.04	K/W	DC operation single side cooled DC operation double side cooled
R <sub>thC-hs</sub> Max. thermal resistance, case to heatsink	0.02 0.01	K/W	DC operation single side cooled DC operation double side cooled
F Mounting force, ± 10%	9800 (1000)	N (Kg)	
wt Approximate weight	83	g	
Case style	TO - 200AB (E-PUK)		See Outline Table

### ΔR<sub>thJ-hs</sub> Conduction

(The following table shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.010	0.011	0.007	0.007	K/W	T <sub>J</sub> = T <sub>J</sub> max.
120°	0.012	0.012	0.012	0.013		
90°	0.015	0.015	0.016	0.017		
60°	0.022	0.022	0.023	0.023		
30°	0.036	0.036	0.036	0.037		

### Ordering Information Table

Device Code							
ST	30	0	C	20	C	1	
①	②	③	④	⑤	⑥	⑦	⑧
<b>1</b>	- Thyristor						
<b>2</b>	- Essential part number						
<b>3</b>	- 0 = Converter grade						
<b>4</b>	- C = Ceramic Puk						
<b>5</b>	- Voltage code: Code x 100 = V <sub>RRM</sub> (See Voltage Rating Table)						
<b>6</b>	- C = Puk Case TO-200AB (E-PUK)						
<b>7</b>	- 0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads)						
	1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads)						
	2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads)						
	3 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)						
<b>8</b>	- Critical dv/dt: None = 500V/μsec (Standard value)						
	L = 1000V/μsec (Special selection)						

Outline Table

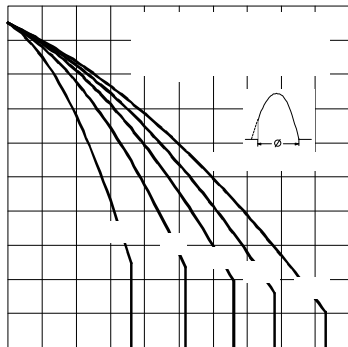
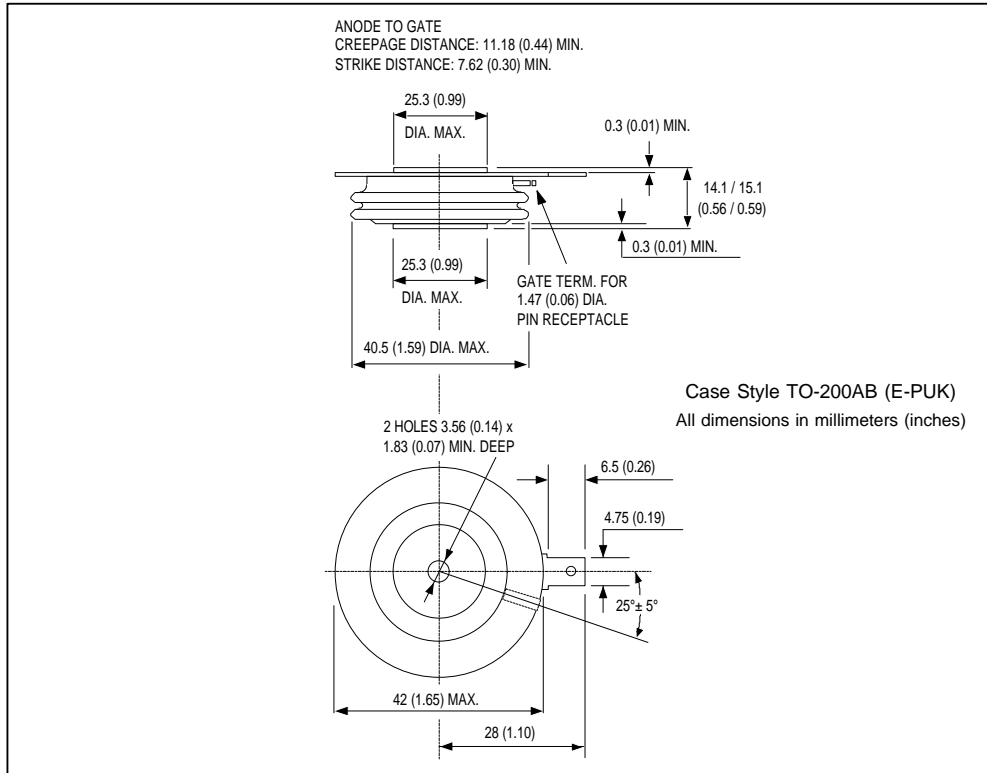


Fig. 1 - Current Ratings Characteristics

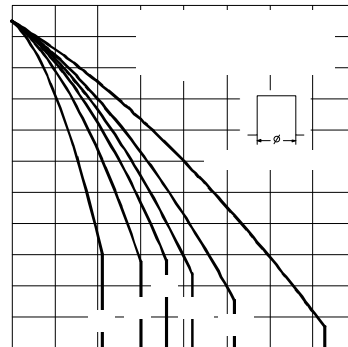


Fig. 2 - Current Ratings Characteristics